GTM CORPORATION

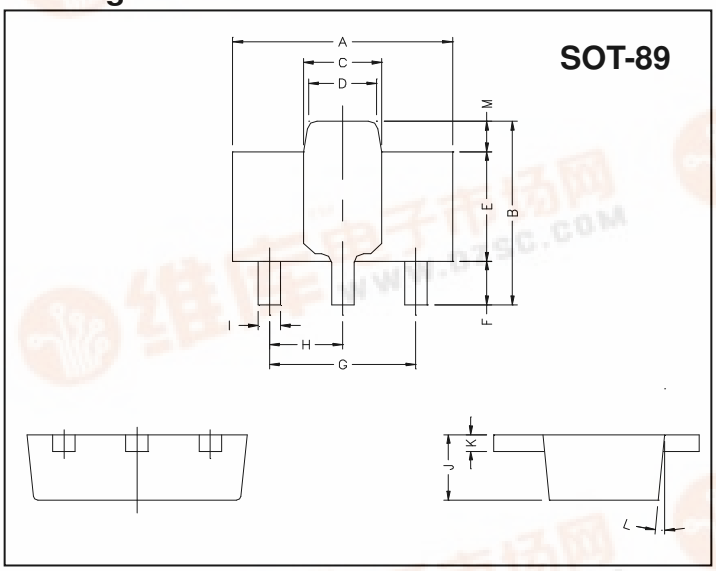
ISSUED DATE :2005/03/25
REVISED DATE :2005/11/28B

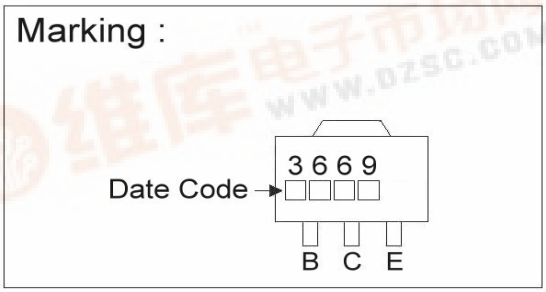
GM3669 NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GM3669 is designed for using in power amplifier applications, power switching application.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.4	4.6	G	3.00 REF.	
B	4.05	4.25	H	1.50 REF.	
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

Absolute Maximum Ratings at T_A = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature Range	T_{STG}	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	5	V
Collect Current(DC)	I_C	2	A
Total Power Dissipation	P_D	1	W

Electrical Characteristics (T_A = 25℃)

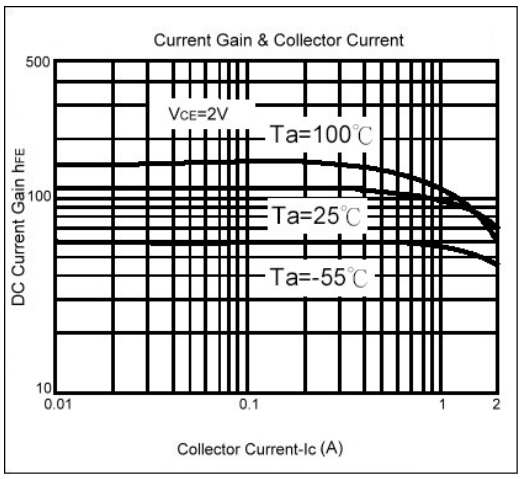
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	80	-	-	V	I_C=100uA, I_E=0
BV_{CEO}	80	-	-	V	I_C=100uA, I_B=0
BV_{EBO}	5	-	-	V	I_E=100uA, I_C=0
I_{CBO}	-	-	1	uA	V_{CB}=80V, I_E=0
I_{EBO}	-	-	1	uA	V_{BE}=5V, I_C=0
*$V_{CE(sat)}$	-	0.15	0.5	V	I_C=1A, I_B=50mA
*$V_{BE(sat)}$	-	0.9	1.2	V	I_C=1A, I_B=50mA
*h_{FE}1	70	-	240		V_{CE}=2V, I_C=0.5A
*h_{FE}2	40	-	-		V_{CE}=2V, I_C=1.5A
fT	-	100	-	MHz	V_{CE}=2V, I_C=0.5A
Cob	-	30	-	pF	V_{CB}=10V, f=1MHz
T_{on}	-	0.2	-	uS	V_{CC}=30V, R_L=30Ω, I_C=1A, I_{B1}=-I_{B2}=50mA, Duty Cycle≦1%
T_{stg}	-	1	-		
T_f	-	0.2	-		

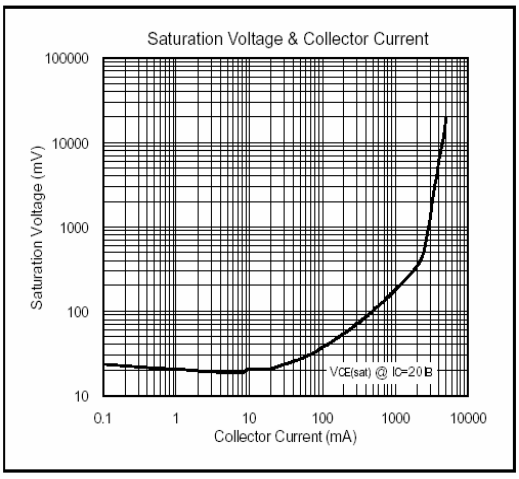
* Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%

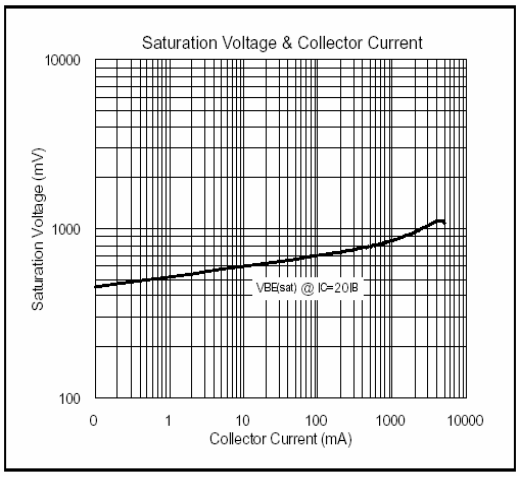
Classification Of h_{FE}1

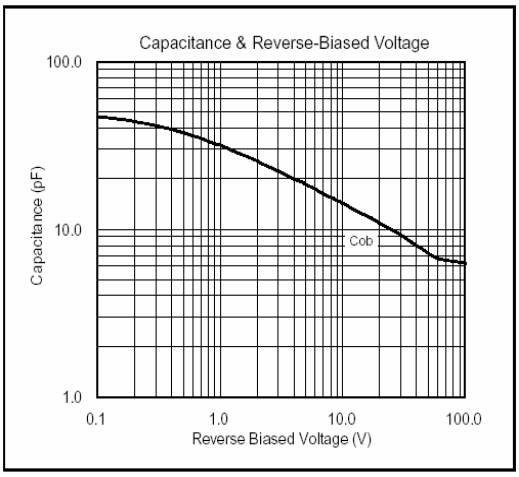
Rank	O	Y
Range	70 ~ 140	120 ~ 240

Characteristics Curve









Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165